

Vishay Siliconix

COMPLIANT

## N-Channel 55-V (D-S), 175 °C MOSFET

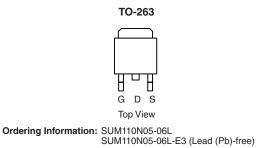
PRODUCT SUMMARY				
V <sub>(BR)DSS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)	
55	0.006 at V <sub>GS</sub> = 10 V	110	65	
55	0.0085 at $V_{GS}$ = 4.5 V	92	05	

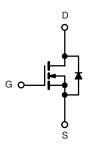
#### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package

#### **APPLICATIONS**

Industrial





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_{C} = 2$	25 °C, unless other	wise noted			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	55	v	
Gate-Source Voltage		V <sub>GS</sub>	± 20	v	
Continuous Drain Current ( $T_1 = 175 ^{\circ}C$ )	T <sub>C</sub> = 25 °C	L	110		
Continuous Drain Current (1) = 175 C)	T <sub>C</sub> = 125 °C	I <sub>D</sub>	63		
Pulsed Drain Current		I <sub>DM</sub>	240	A	
Avalanche Current		I <sub>AR</sub>	60		
Repetitive Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AR</sub>	180	mJ	
Manimum Davies Dissignation	T <sub>C</sub> = 25 °C	р. 158 <sup>b</sup>		w	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C <sup>c</sup>	P <sub>D</sub>	3.7	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Limit	Unit	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W	
Junction-to-Case		R <sub>thJC</sub>	0.95	C/W	

Notes:

a. Duty cycle  $\leq$  1 %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{DS} = 0 V, I_{D} = 250 \mu A$	55			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1		3		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 55 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1		
		$V_{DS} = 55 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50	μA	
		$V_{DS} = 55 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$			250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	120			А	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A		0.0047	0.006	Ω	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0066	0.0085		
	r <sub>DS(on)</sub>	$V_{GS}$ = 10 V, I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C			0.0102		
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}, \text{ T}_{J} = 175 ^{\circ}\text{C}$			0.0132		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	30			S	
Dynamic <sup>b</sup>	•			•	ι      ι		
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		3300		pF	
Output Capacitance	C <sub>oss</sub>			625			
Reverse Transfer Capacitance	C <sub>rss</sub>			310			
Total Gate Charge <sup>c</sup>	Qg			65	100	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 30$ V, $V_{GS} = 10$ V, $I_{D} = 110$ A		15			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			16			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			15	25		
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{DD} = 30 \text{ V},  R_L = 0.27 \ \Omega \\ I_D \cong 110 \ A,  V_{GEN} = 10 \ V,  R_g = 2.5 \ \Omega \end{array}$		15	25	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			35	55		
Fall Time <sup>c</sup>	t <sub>f</sub>			15	25		
Source-Drain Diode Ratings and Cha	aracteristics 7	<sub>C</sub> = 25 °C <sup>b</sup>			<u> </u>		
Continuous Current	ا <sub>S</sub>				110		
Pulsed Current	I <sub>SM</sub>				240	A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 110 A, V <sub>GS</sub> = 0 V		1.0	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			70	125	ns	
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>	I <sub>F</sub> = 110 A, di/dt = 100 A/μs		2.5	5	А	
Reverse Recovery Charge	Q <sub>rr</sub>			0.09	0.31	μC	

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

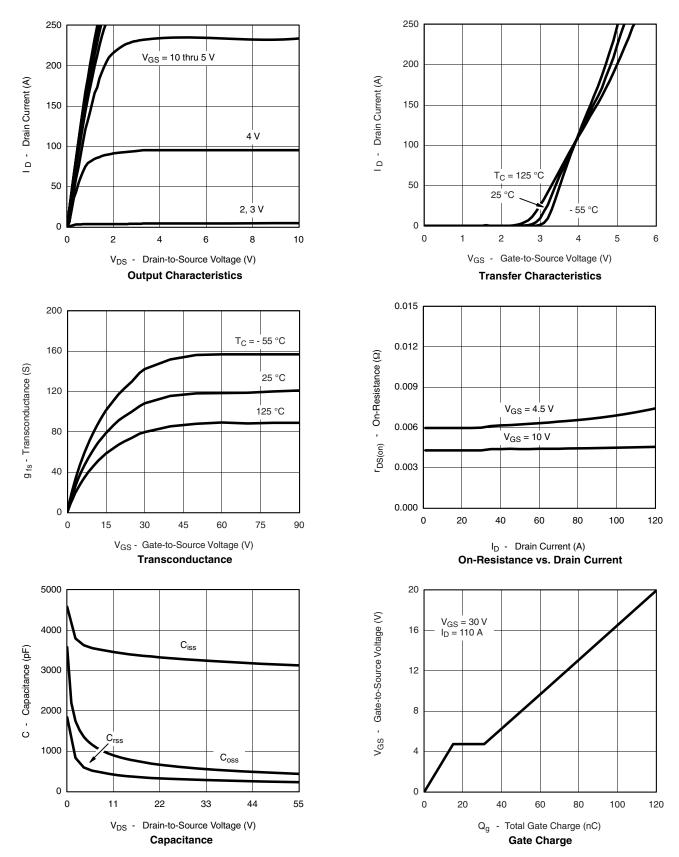
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

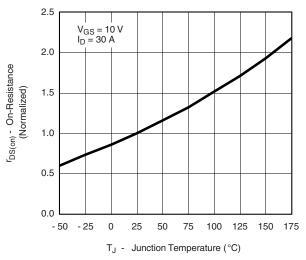


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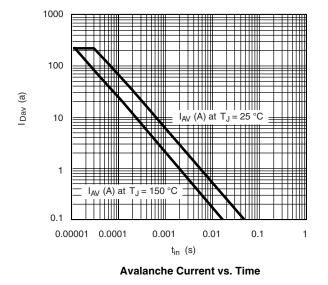


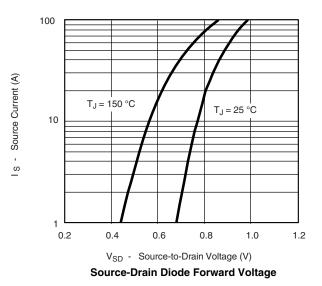
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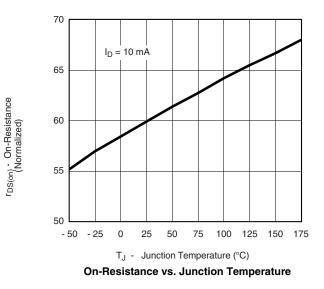
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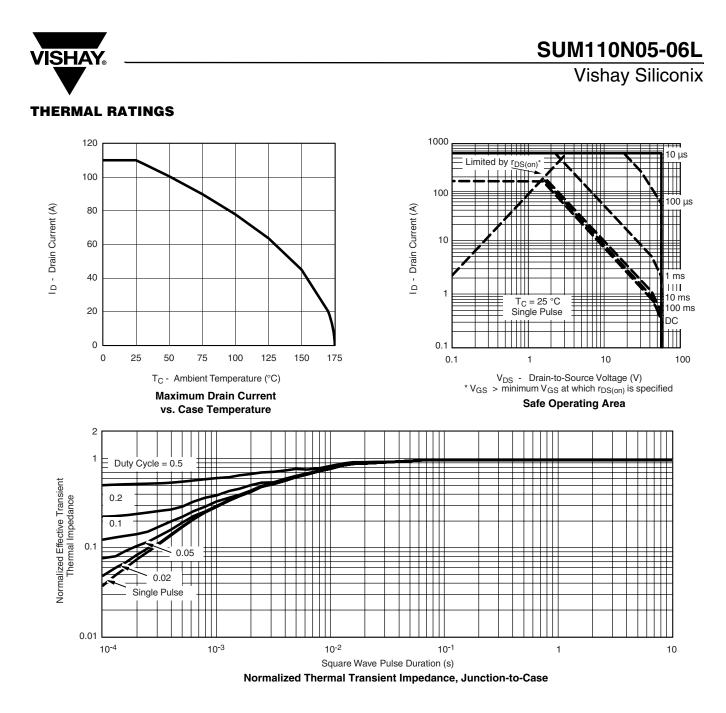


On-Resistance vs. Junction Temperature









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